

Magnetic bound states embedded in tantalum superconducting thin films

Soroush Arabi,^{1,2,a)} Qili Li,² Ritika Dhundhwal,¹ Dirk Fuchs,¹ Thomas Reisinger,¹ Ioan M. Pop,^{1,2,3} and Wulf Wulfhekel^{1,2}

¹⁾Institute for Quantum Materials and Technologies, Karlsruhe Institute of Technology, 76131 Karlsruhe, Germany

²⁾Physikalisches Institut, Karlsruhe Institute of Technology, 76131 Karlsruhe, Germany

³⁾Physics Institute 1, Stuttgart University, 70569 Stuttgart, Germany

In the fabrication of superconducting devices, both *in situ* and *ex situ* processes are utilized, making the removal of unwanted oxide layers and impurities under vacuum conditions crucial. Oxygen descumming and argon milling are standard *in situ* cleaning methods employed for device preparation. We investigated the impact of these techniques on tantalum superconducting thin films using scanning tunneling microscopy at millikelvin temperatures. We demonstrate that these cleaning methods inadvertently introduce magnetic bound states within the superconducting gap of tantalum, likely by oxygen impurities. These bound states can be detrimental to superconducting qubit devices, as they add to dephasing and energy relaxation.

The quest for quantum computing platforms capable of realizing reliable and scalable qubit devices has spurred intensive research efforts in the last decades^{1,2}. A key strategy driving progress in this area is the synergistic integration of diverse materials, leveraging their distinct advantages^{3,4}. One notable example is the tantalum transmon qubit⁵, which incorporates tantalum for the capacitive elements due to its well-behaved surface oxide⁶ and compatibility with harsh cleaning methods, while aluminum is utilized for the Josephson junction, thanks to its stable and controllable thermal oxide. However, the fabrication process presents a significant challenge: it involves two separate lithography steps, which expose the tantalum surface to air, introducing surface contamination and oxidation (see Figure 1a).

Maintaining a pristine tantalum contact surface and a clean tantalum-aluminum interface is essential to ensure a high-quality circuit. This requires the effective removal of e-beam residues from lithography and the oxide layer that forms after breaking the vacuum. Traditionally, to connect the tantalum and aluminum layers, a step of oxygen descumming (plasma/ash) followed by argon milling of the tantalum layer is used. Oxygen plasma effectively volatilizes organic materials, such as residual e-beam resist molecules, aiding in their removal but simultaneously promoting additional surface oxidation. Argon milling is then employed to remove both the oxide layers and any remaining volatile organic molecules, with the goal of achieving a pristine contact surface for subsequent aluminum deposition. Our study, however, reveals an unanticipated consequence of this cleaning procedure: the creation of magnetic bound states at the interface by argon milling, which can act as a source of spurious two-level systems and pose further challenges to qubit performance.

When tantalum is exposed to air, its surface becomes covered by a fully oxidized Ta_2O_5 layer, renowned for its stability and insulating properties⁶⁻⁸. Beneath this oxide layer, suboxide species such as Ta^{3+} and Ta^{1+} exist in minor quantities within an amorphous transition region between the oxide and the metallic bulk⁶. The removal of the surface oxide by Ar^+ milling involves a stochastic scattering process, which

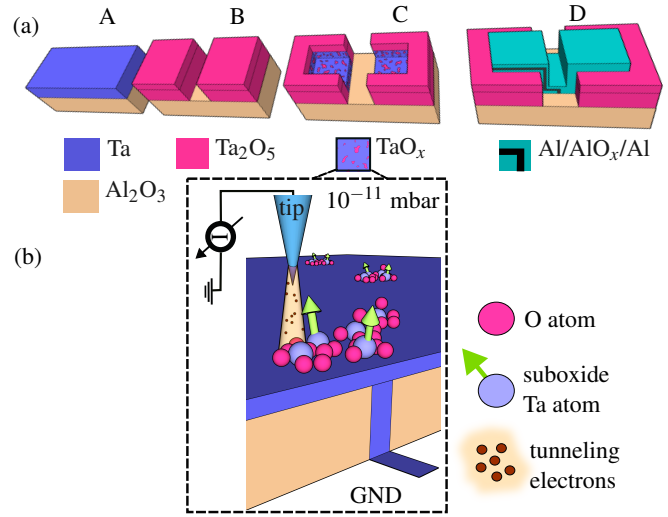


FIG. 1. Schematic overview of the main steps in tantalum qubit metallization and the principle of STM measurements. (a) The metallization process begins with the Al_2O_3 substrate (sand brown) undergoing solvent cleaning. Next, tantalum (majorelle blue) is sputtered onto the substrate using DC magnetron sputtering at 600°C in UHV (A). In (B), the substrate exits UHV for patterning and additional cleaning, during which a layer of Ta_2O_5 (red pink) forms. The sample is then returned to UHV for a cleaning protocol that combines O_2 plasma treatment and argon milling (C). Argon milling does not fully remove the native oxides, leaving non-stoichiometric TaO_x traces (blue-red mix) on or near the surface. The final step (D) involves the deposition of aluminum (cyan), aluminum oxide (black), and aluminum to form Josephson junctions. (b) Scanning tunneling microscopy (STM) is performed on the TaO_x traces using a superconducting Ta tip at 45 mK. The tantalum sample is connected to the ground (GND) via a side-contact.

can generate vacancies, interstitials, and impurities within the tantalum film. In particular, intermixed oxygen can induce localized states in the thin film with charge and spin degrees of freedom⁹⁻¹³. While aiming for the complete removal of the oxide layer, intensive Ar^+ milling may introduce numerous defects in both the film and the substrate, whereas moderate milling typically leaves traces of these localized states.

Here, we demonstrate that argon milling of oxidized tantalum films induces defects on the surface of the thin film,

^{a)}Corresponding author: soroush.arabi@kit.edu

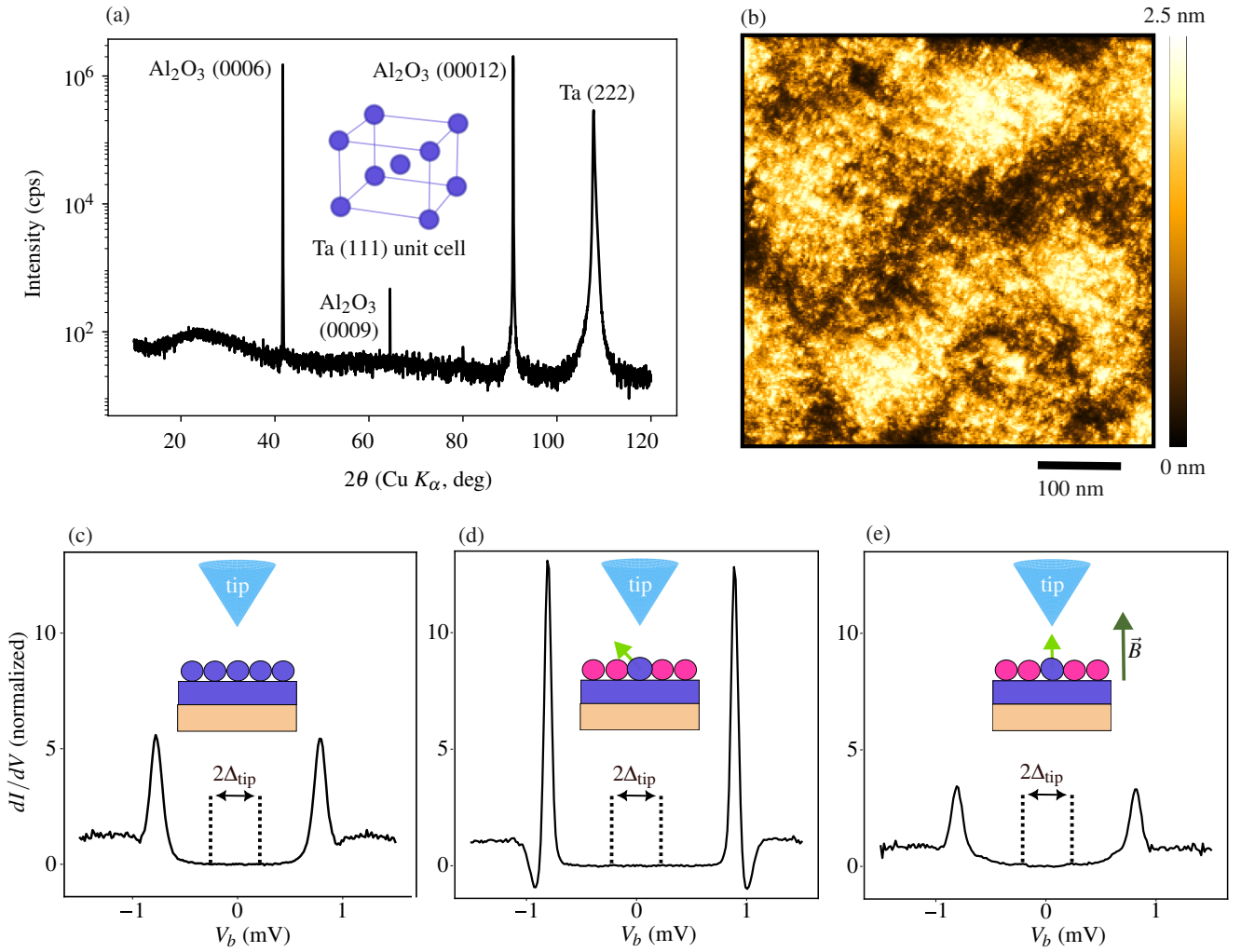


FIG. 2. XRD and STM characterization of an $\alpha(111)$ tantalum film. (b) XRD spectrum of the tantalum film grown on c-plane Al_2O_3 . The diffraction pattern reveals a single Ta peak, labeled as $\alpha(222)$, indicating the α phase growing in the (111) direction. The $\alpha(111)$ peak is suppressed in diffractograms of BCC crystals (unit cell shown in the inset). A narrow peak at 65° corresponds to diffraction from residual K_β X-rays originating from the sapphire substrate. (b) STM topography acquired at a bias voltage $V_b = 100$ mV and a current setpoint $I_p = 90$ pA. (c) Representative dI/dV spectrum displaying the pristine superconducting gap of the combined Ta sample and tip. (d) dI/dV spectrum measured on a suboxide region, showing a pair of effective $S = 1/2$ YSR states with a binding energy of $597.5 \mu\text{eV}$ after Ar^+ milling. (e) dI/dV spectrum obtained from the same suboxide region as in (d) under an 17 mT out-of-plane magnetic field. The YSR peaks are suppressed, and the coherence peaks of the sample are reduced compared to (c). Measurements were conducted at $V_b = 1.5$ mV, $I_p = 100$ pA, and base temperature of $T = 45$ mK using a lock-in technique with a modulation frequency of 3.3 kHz and an AC bias modulation amplitude of $V_{\text{mod}} = 20 \mu\text{V}$. The spectra incorporate the combined SIS gap for the tantalum film and tip, with $\Delta_{\text{sample}} = 600.3 \mu\text{eV}$ and $\Delta_{\text{tip}} = 208.1 \mu\text{eV}$.

which, in close proximity to the tantalum superconductor, give rise to localized magnetic bound states, known as Yu-Shiba-Rusinov (YSR) states^{14–16}. These states represent low-energy excitations within the superconducting energy which can be measured directly by a local probe (see Figure 1b). The localized magnetic moments exert an exchange interaction J on the Cooper pairs in the superconducting condensate. Depending on the strength of J , either the Cooper pairs are broken and the local spin is screened by normal electrons, similar to the Kondo effect (for $\Delta < J$), or the local spin remains un-screened, exerting a small effective field on the Cooper pairs (for $J < \Delta$). The excitation between these two states costs less energy than Δ and manifests itself as a YSR state within the

superconducting gap^{17,18}.

The energy of the YSR states is primarily determined by the strength of the exchange coupling, neglecting the Coulomb scattering effect. It is expressed as $\epsilon = \pm\Delta \frac{1-\alpha^2}{1+\alpha^2}$, where $\alpha = JS_{\text{imp}}\pi\rho_n$, with S_{imp} the local moment spin and ρ_n the density of normal electronic states at the Fermi level¹⁹. In tunneling spectroscopy dI/dV , YSR states appear as prominent peaks symmetrically located within the energy gap for $J/\Delta \neq 0$. As $J/\Delta \rightarrow 0$, they shift toward the quasiparticle coherence peaks at $\epsilon \approx \pm\Delta$, representing an almost free-spin state. The number of peaks increases as the local moment spin increases, from a single pair for spin-1/2 to multiple pairs for

higher spin states^{20,21}.

We prepared the sample by depositing 200 nm tantalum film on a c-plane sapphire (Al_2O_3) substrate at 600°C using DC magnetron sputtering, resulting in textured film of the α phase oriented predominantly with the epitaxial alignment $(0001) \text{Al}_2\text{O}_3 \parallel (111) \text{Ta}$. To determine the crystallographic phase and growth direction of the film, we performed X-ray diffraction (XRD) on the sample. We obtained a 2θ scan using a monochromatized characteristic X-ray K_α line from a Cu source. The XRD spectrum (Figure 2a) shows the presence of α phase growing in (111) direction, which is thermodynamically stable and has body-centered cubic structure.

After exposure to air, a native tantalum oxide layer formed on the surface. The sample was then transferred to an ultrahigh vacuum (UHV) chamber for Ar^+ milling in 15- and 30-minute intervals. The milling process utilized a differentially pumped extractor-type ion source (SPECS IQE 12/38), delivering an ion beam current density of $3.2 \mu\text{A}/\text{cm}^2$ at the sample plate with a primary ion energy of 3 keV. The chamber pressure was maintained at $\sim 2 \times 10^{-8}$ mbar throughout the milling procedure. Without breaking the UHV, the sample was subsequently transferred to the scanning tunneling microscope (STM) for surface characterization at 45 mK using a superconducting tantalum-coated tip²². The superconducting tip was prepared by indentation of a tungsten tip on the Ta surface. To enable charge transport in the STM experiments, the samples included a side contact with the ground.

We characterized the surface of the air-exposed tantalum sample after 15 minutes of Ar^+ milling. The STM topography (Figure 2b) reveals a surface with a root-mean-square roughness of only 445.1 pm over an area of $0.5 (\mu\text{m})^2$. Differential conductance (dI/dV) measurements on the bare tantalum surface (Figure 2c) indicate a combined superconducting gap ($2\Delta_{\text{tot.}} = 2\Delta_{\text{sample}} + 2\Delta_{\text{tip}}$) characteristic for tunneling between two superconductors, i.e., in a superconductor-insulator-superconductor (SIS) tunnel junction. To disentangle the contributions of the sample and tip to the SIS spectrum, we performed dI/dV measurements in an out-of-plane magnetic field (see supplementary Figure S1). We extracted zero-field superconducting gaps of $\Delta_{\text{sample},0} = 600.3 \mu\text{eV}$ and $\Delta_{\text{tip},0} = 208.1 \mu\text{eV}$, with corresponding critical fields of $B_{\text{sample,c}} = 103.1 \text{ mT}$ and $B_{\text{tip,c}} = 1.59 \text{ T}$ for sample and tip. The surface gap is slightly smaller than the bulk value of $\Delta_{\text{bulk}} \approx 720 \mu\text{eV}$ for α phase tantalum^{23–25}, likely due to small grain size and surface disorder. Furthermore, we frequently observed sharp and prominent single-pair YSR states, positioned asymptotically close to the quasiparticle coherence peaks that dominate the spectrum (Figure 2d). In an out-of-plane magnetic field, the YSR states became polarized and vanished at 17 mT, accompanied by a smearing of the coherence peaks of the superconducting gap (Figure 2e). In an attempt to eliminate regions containing YSR states, likely originating from Ar^+ milling defects, we extended the milling process for an additional 30 minutes. Surprisingly, this resulted in the observation of numerous regions exhibiting YSR states with a double-pair structure. The inner (smaller) and outer (larger) pairs exhibited binding energies of $410.2 \mu\text{eV}$ and $598.4 \mu\text{eV}$, respectively, suggesting the presence of local-

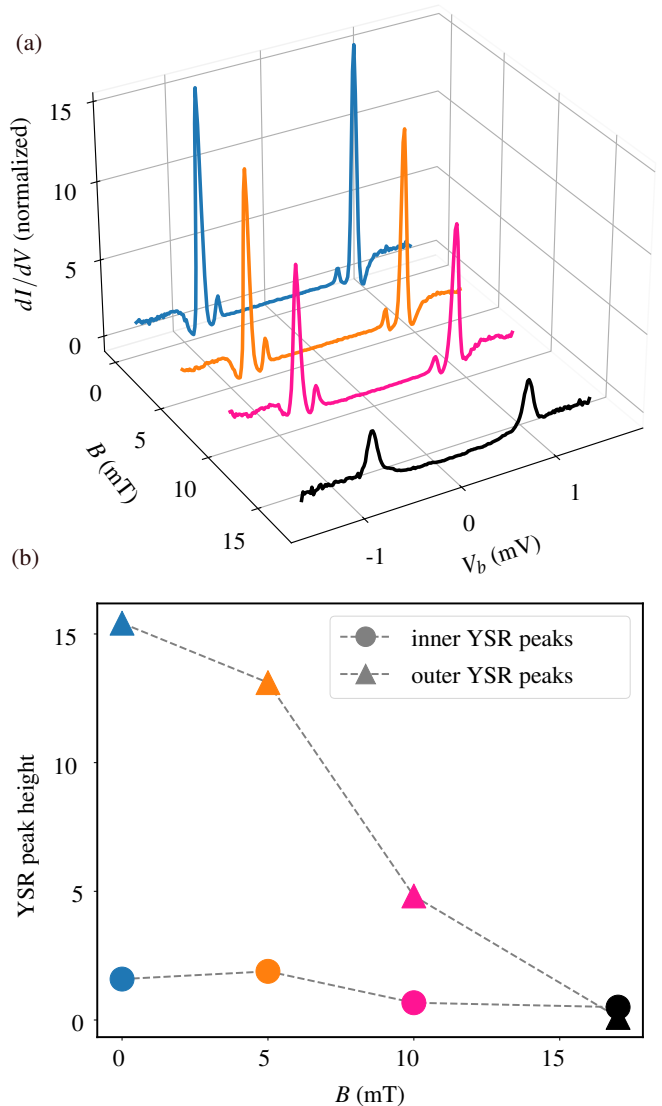


FIG. 3. Magnetic field dependence of an effective $S = 3/2$ YSR state embedded in suboxide regions of $\alpha(111)$ tantalum. (a) Evolution of dI/dV spectra of the YSR states in response to out-of-plane magnetic fields, leading to the suppression of the YSR states and the resurgence of the superconducting order parameter at approximately 18 mT. The dashed vertical lines on the side wall represent the projection of the average YSR peak heights. (b) Extracted peak values of the dI/dV spectra of the outer (larger) and inner (smaller) YSR states. Measurements were obtained at a fixed tip position under the following conditions: bias voltage $V_b = 1.5 \text{ mV}$, current setpoint $I_p = 100 \text{ pA}$, lock-in modulation voltage $V_{\text{mod}} = 20 \mu\text{V}$ and temperature $T = 45 \text{ mK}$, utilizing a superconducting tip with $\Delta_{\text{tip}} = 208.1 \mu\text{eV}$.

ized spins with higher angular momentum (Figure 3a). We then applied an out-of-plane magnetic field, which gradually suppressed the excitations and pushed them outside the superconducting gap, ultimately removing them entirely at approximately 18 mT (Figure 3b). This behavior aligns with the characteristics of YSR states extended over a large area with significant magnetic anisotropy, as has been discussed

in detail in Ref.²⁶. Similar YSR states detrimental to the superconducting gap have been observed with STM in granular Aluminum due to the non-stoichiometric aluminumoxide¹¹.

In conclusion, our study reveals the unintended consequences of commonly employed cleaning procedures, such as oxygen descumming and argon milling, in the fabrication of tantalum-based superconducting qubits. Although these techniques are critical for preparing the surface and ensuring high-quality Josephson junctions, they also introduce oxygen defects that give rise to magnetic impurities. These impurities, in turn, host YSR bound states within the superconducting gap, which degrade the coherence and performance of tantalum qubits. Our observations highlight the necessity of revisiting and refining the cleaning protocols in qubit fabrication. A delicate balance must be achieved between the removal of oxide layers and the preservation of the pristine superconducting properties of tantalum thin films. An alternative approach could be the use of noble metal passivation layers to prevent the formation of native tantalum oxides in the first place²⁷.

ACKNOWLEDGMENTS

This work was supported by the German Ministry of Education and Research (BMBF) within the project QSolid (FKZ:13N16151).

AUTHOR DECLARATIONS

Conflict of Interest

The authors declare that there are no conflicts of interest.

AUTHOR CONTRIBUTIONS

Soroush Arabi: Investigation (lead); Conceptualization (equal); Data curation (lead); Formal analysis (lead); Methodology (lead); Validation (lead); Visualization (lead); Project administration (lead); Writing - original draft (lead); Writing - review & editing (lead). **Qili Li:** Investigation (equal); Writing - review & editing (equal). **Ritika Dhundhwal:** Investigation (equal); Data curation (equal); Writing - review & editing (equal). **Dirk Fuchs:** Investigation (equal). **Thomas Reisinger:** Conceptualization (equal); Methodology (equal); Writing - review & editing (equal). **Ioan Pop:** Conceptualization (equal); Methodology (equal); Writing - review & editing (equal); Resources (equal); Funding acquisition (equal); Supervision (equal). **Wulf Wulfhekel:** Conceptualization (equal); Methodology (equal); Writing - review & editing (equal); Resources (equal); Funding acquisition (equal); Supervision (equal)

DATA AVAILABILITY

Data supporting the findings of this study are available from the corresponding author upon reasonable request.

- ¹A. Blais, A. L. Grimsmo, S. M. Girvin, and A. Wallraff, *Rev. Mod. Phys.* **93**, 025005 (2021).
- ²I. Siddiqi, *Nature Reviews Materials* **6**, 875 (2021).
- ³N. P. de Leon, K. M. Itoh, D. Kim, K. K. Mehta, T. E. Northup, H. Paik, B. S. Palmer, N. Samarth, S. Sangtawesin, and D. W. Steuerman, *Science* **372**, eabb2823 (2021).
- ⁴X. Liu and M. C. Hersam, *Nature Reviews Materials* **4**, 669 (2019).
- ⁵A. P. M. Place, L. V. H. Rodgers, P. Mundada, B. M. Smitham, M. Fitzpatrick, Z. Leng, A. Premkumar, J. Bryon, A. Vrajitoarea, S. Sussman, G. Cheng, T. Madhavan, H. K. Babla, X. H. Le, Y. Gang, B. Jäck, A. Geynis, N. Yao, R. J. Cava, N. P. de Leon, and A. A. Houck, *Nature Communications* **12**, 1779 (2021).
- ⁶R. A. McLellan, A. Dutta, C. Zhou, Y. Jia, C. Weiland, X. Gui, A. P. M. Place, K. D. Crowley, X. H. Le, T. Madhavan, Y. Gang, L. Baker, A. R. Head, I. Waluyo, R. Li, K. Kisslinger, A. Hunt, I. Jarrige, S. A. Lyon, A. M. Barbour, R. J. Cava, A. A. Houck, S. L. Hulbert, M. Liu, A. L. Walter, and N. P. de Leon, *Advanced Science* **10**, 2300921 (2023).
- ⁷R. A. B. Devine, L. Vallier, J. L. Autran, P. Paillet, and J. L. Leray, *Applied Physics Letters* **68**, 1775 (1996).
- ⁸C. Chaneliere, J. Autran, R. Devine, and B. Balland, *Materials Science and Engineering: R: Reports* **22**, 269 (1998).
- ⁹M. V. Ivanov, T. V. Perevalov, V. S. Aliev, V. A. Gritsenko, and V. V. Kaichev, *Journal of Applied Physics* **110**, 024115 (2011).
- ¹⁰T. Shu, Y. Cui, C. Tao, D. Feng, Y. Zhao, and J. Shao, *Opt. Mater. Express* **12**, 4547 (2022).
- ¹¹F. Yang, T. Gozliniski, T. Storbeck, L. Grünhaupt, I. M. Pop, and W. Wulfhekel, *Phys. Rev. B* **102**, 104502 (2020).
- ¹²R. Ramprasad, *Journal of Applied Physics* **94**, 5609 (2003).
- ¹³I. Perez, V. Sosa, F. G. Perera, J. T. Elizalde Galindo, J. L. Enríquez-Carrejo, and P. G. Mani González, *Vacuum* **165**, 274 (2019).
- ¹⁴L. Yu, *Acta Physica Sinica* **21**, 75 (1965).
- ¹⁵H. Shiba, *Progress of Theoretical Physics* **40**, 435 (1968).
- ¹⁶A. I. Rusinov, *JETP Lett. (USSR)* **9** (1969).
- ¹⁷M. E. Flatté and J. M. Byers, *Phys. Rev. Lett.* **78**, 3761 (1997).
- ¹⁸L. Farinacci, G. Ahmadi, G. Reecht, M. Ruby, N. Bogdanoff, O. Peters, B. W. Heinrich, F. von Oppen, and K. J. Franke, *Phys. Rev. Lett.* **121**, 196803 (2018).
- ¹⁹A. V. Balatsky, I. Vekhter, and J.-X. Zhu, *Rev. Mod. Phys.* **78**, 373 (2006).
- ²⁰M. Ruby, F. Pientka, Y. Peng, F. von Oppen, B. W. Heinrich, and K. J. Franke, *Phys. Rev. Lett.* **115**, 087001 (2015).
- ²¹R. Žitko, O. Bodensiek, and T. Pruschke, *Phys. Rev. B* **83**, 054512 (2011).
- ²²T. Balashov, M. Meyer, and W. Wulfhekel, *Rev. Sci. Instrum.* **89**, 113707 (2018).
- ²³J. J. Hauser and H. C. Theuerer, *Rev. Mod. Phys.* **36**, 80 (1964).
- ²⁴K. D. Crowley, R. A. McLellan, A. Dutta, N. Shumiya, A. P. M. Place, X. H. Le, Y. Gang, T. Madhavan, M. P. Bland, R. Chang, N. Khedkar, Y. C. Feng, E. A. Umbarkar, X. Gui, L. V. H. Rodgers, Y. Jia, M. M. Feldman, S. A. Lyon, M. Liu, R. J. Cava, A. A. Houck, and N. P. de Leon, *Phys. Rev. X* **13**, 041005 (2023).
- ²⁵T. A. J. van Schijndel, A. P. McFadden, A. N. Engel, J. T. Dong, W. J. Yáñez-Parreño, M. Parthasarathy, R. W. Simmonds, and C. J. Palmström, “Cryogenic growth of tantalum thin films for low-loss superconducting circuits,” (2024), arXiv:2405.12417 [cond-mat.supr-con].
- ²⁶T. Machida, Y. Nagai, and T. Hanaguri, *Phys. Rev. Res.* **4**, 033182 (2022).
- ²⁷R. D. Chang, N. Shumiya, R. A. McLellan, Y. Zhang, M. P. Bland, F. Bahrami, J. Mun, C. Zhou, K. Kisslinger, G. Cheng, A. C. Pakpour-Tabrizi, N. Yao, Y. Zhu, M. Liu, R. J. Cava, S. Gopalakrishnan, A. A. Houck, and N. P. de Leon, “Eliminating surface oxides of superconducting circuits with noble metal encapsulation,” (2024), arXiv:2408.13051.

Supplemental Material

Magnetic Bound States Embedded in Tantalum Superconducting Thin Films

Soroush Arabi^{*1,2}, Qili Li², Ritika Dhundhwal¹, Dirk Fuchs¹, Thomas Reisinger¹,
Ioan M. Pop^{1,2,3}, and Wulf Wulfhekel^{1,2}

¹Institute for Quantum Materials and Technologies, Karlsruhe Institute of Technology, 76131 Karlsruhe, Germany

²Physikalisches Institut, Karlsruhe Institute of Technology, 76131 Karlsruhe, Germany

³Physics Institute 1, Stuttgart University, 70569 Stuttgart, Germany

In this supplementary material, we provide detailed information on the characterization of the superconducting tunnel junction used in the STM measurements to determine the superconducting gap and critical magnetic field of the $\alpha(111)$ tantalum thin film, as reported in the main text.

*Corresponding author: soroush.arabi@kit.edu

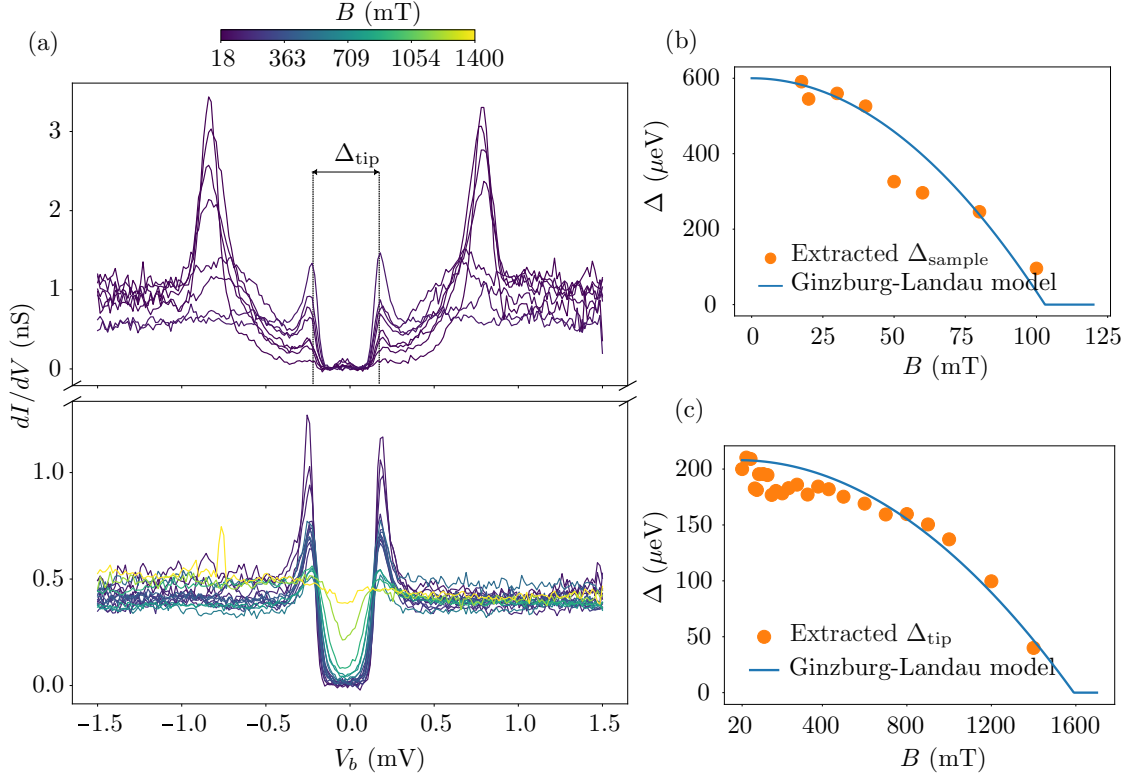


FIG. S1: Characterization of the SIS tunnel junction under an applied magnetic field. **(a)** Evolution of the dI/dV spectra of the SIS tunnel junction as a function of out-of-plane magnetic fields, revealing the superconducting gaps of both the sample and the tip. **(b)** Superconducting gap of the tantalum thin film as a function of magnetic field. **(c)** Superconducting gap of the tantalum tip as a function of magnetic field. The superconducting gaps for both the sample and the tip were extracted from each dI/dV spectrum using the Dynes formula. The measurements in **(b)** and **(c)** were fitted using the Landau-Ginzburg model, $\Delta/\Delta_0 = 1 - (B/B_c)^2$, yielding zero-field superconducting gaps of $\Delta_{\text{sample},0} = 600.3 \mu\text{eV}$ and $\Delta_{\text{tip},0} = 208.1 \mu\text{eV}$, with critical fields of $B_{\text{sample},c} = 103.1 \text{ mT}$ and $B_{\text{tip},c} = 1.59 \text{ T}$, respectively. The dI/dV measurements were taken at a fixed tip position under the following conditions: bias voltage $V_b = 1.5 \text{ mV}$, current setpoint $I_p = 100 \text{ pA}$, lock-in modulation voltage $V_{\text{mod}} = 20 \mu\text{V}$, and temperature $T = 45 \text{ mK}$.

S1. Characterization of the SIS Tunnel Junction

We extract the superconducting gap and critical magnetic field of $\alpha(111)$ Ta based on the method explained in Figure S1. We performed dI/dV measurements in an out-of-plane magnetic field. The dI/dV spectrum evolved from a double-gap structure at low magnetic fields for the combined gaps (Figure S1a, top panel), to a conventional BCS-like single-gap spectrum at higher magnetic fields, representing the tip's superconducting gap (Figure S1a, bottom panel).

The superconducting gap at each magnetic field was determined by fitting the spectrum with the Dynes function¹, after which the measured gaps as a function of magnetic field were fit using the Ginzburg-Landau model^{2,3} (Figure S1b and S1c). This analysis yielded zero-field superconducting gaps of $\Delta_{\text{sample},0} = 600.3 \mu\text{eV}$ and $\Delta_{\text{tip},0} = 208.1 \mu\text{eV}$, with corresponding critical fields of $B_{\text{sample},c} = 101.7 \text{ mT}$ and $B_{\text{tip},c} = 1.51 \text{ T}$. Notably, the critical field of the sharp superconducting tip is much larger than that of the sample, owing to the much smaller size of the tip's apex and the correspondingly smaller magnetic flux passing through it.

References

[1] R. C. Dynes, V. Narayanamurti, and J. P. Garno, Phys. Rev. Lett. **41**, 1509 (1978).

[2] R. C. Casella and P. B. Miller, Phys. Rev. **136**, A928 (1964).

[3] R. Meservey and D. H. Douglass, Phys. Rev. **135**, A24 (1964).